

# BAT54P

## SCHOTTKY BARRIER DIODE

### Features

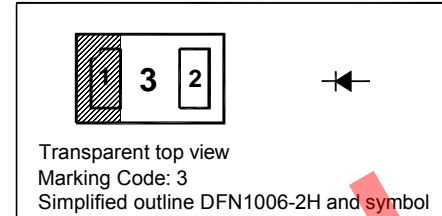
- Low forward voltage

### Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

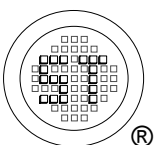


### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

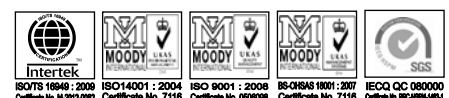
Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Forward Current	$I_F$	200	mA
Repetitive Peak Forward Current	$I_{FRM}$	300	mA
Peak Forward Surge Current ( $t_p = 10$ ms)	$I_{FSM}$	600	mA
Power Dissipation	$P_D$	250	mW
Thermal Resistance from Junction Ambient	$R_{thJA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Max.	Unit
Forward Voltage at $I_F = 0.1$ mA at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 30$ mA at $I_F = 100$ mA	$V_F$	-	0.24 0.32 0.4 0.5 0.8	V
Reverse Breakdown Voltage at $I_R = 10$ $\mu\text{A}$	$V_{(BR)R}$	30	-	V
Reverse Current at $V_R = 25$ V	$I_R$	-	2	$\mu\text{A}$
Total Capacitance at $V_R = 1$ V, $f = 1$ MHz	$C_T$	-	10	pF
Reverse Recovery Time at $I_F = 10$ mA, $V_R = 6$ V, $I_R = 10$ mA, $R_L = 100$ $\Omega$	$t_{rr}$	-	6	ns



**SEMTECH ELECTRONICS LTD.**  
Subsidiary of Sino-Tech International (BVI) Limited



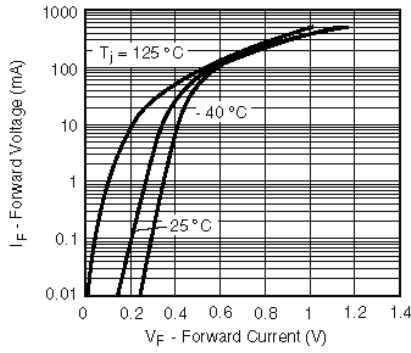


Figure 1. Typical Forward Voltage Forward Current at Various Temperatures

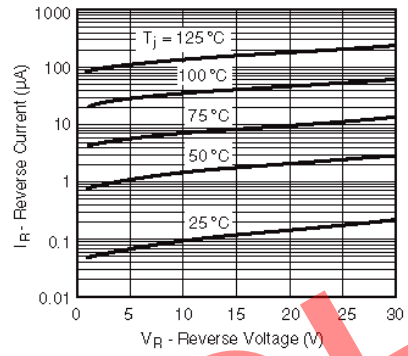


Figure 3. Typical Variation of Reverse Current at Various Temperatures

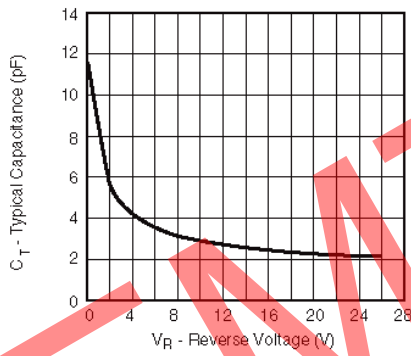
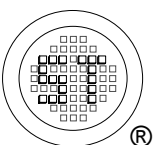


Figure 2. Typical Capacitance vs. Reverse Applied Voltage  $V_R$

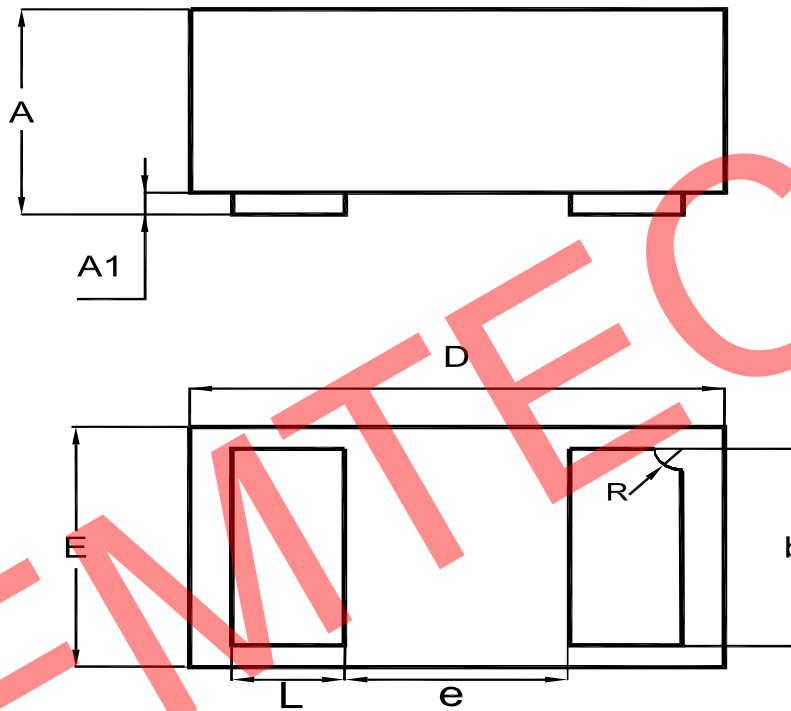


# BAT54P

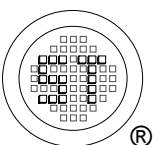
## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51	0.05	0.55	1.075	0.675	0.4	0.3	0.15
	0.46	0	0.45	0.95	0.55		0.2	0.05



**SEMTECH ELECTRONICS LTD.**  
Subsidiary of Sino-Tech International (BVI) Limited



Dated: 03/07/2013 Rev: 01